

S-5855A Series

PWM OUTPUT TEMPERATURE SENSOR IC

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Rev.1.2_01

The S-5855A Series, developed by CMOS technology, is a 1-wire PWM output temperature sensor IC of low current consumption that itself changes the duty ratio according to temperature.

The duty ratio decreases from 100% if exceeding the temperature set by user, and this decrease is linear against the temperature rise.

The output form is selectable from CMOS output and Nch open-drain output.

Its small packages SNT-4A and SOT-23-5 enable high-density mounting.

■ Features

• PWM output : 1-wire PWM interface

• Temperature accuracy : ±3.0°C

Duty ratio change-start temperature
 Selectable from +40°C to +80°C in 10°C step
 Duty ratio temperature sensitivity
 Selectable from -1 %/°C to -4 %/°C in 1 %/°C step

• Low current consumption : $50 \mu A \text{ typ.}$ (Ta = $+25^{\circ}C$)

• Low power supply voltage : 1.65 V to 5.5 V

• Wide range of operation temperature : Ta = -40°C to +125°C

• Lead-free (Sn 100%), halogen-free

■ Application

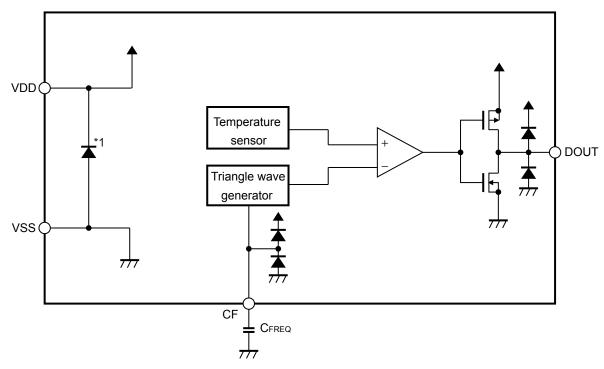
• Temperature compensation for LED instruments

■ Packages

- SNT-4A
- SOT-23-5

■ Block Diagrams

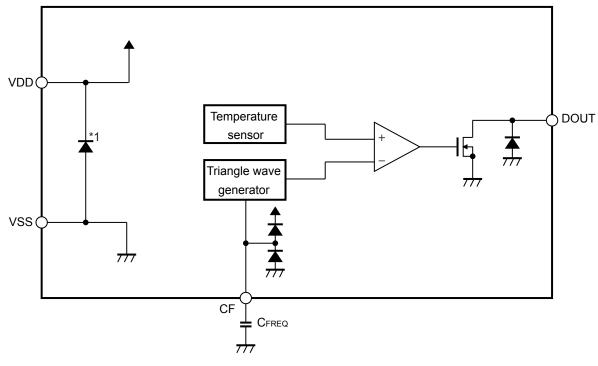
1. CMOS output product



*1. Parasitic diode

Figure 1

2. Nch open-drain output product

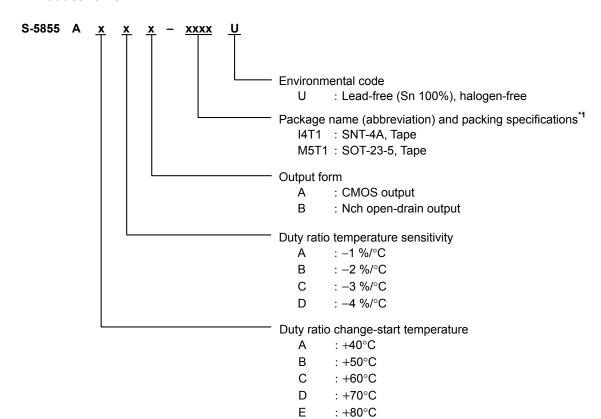


*1. Parasitic diode

Figure 2

■ Product Name Structure

1. Product name



^{*1.} Refer to the tape drawing.

2. Packages

Dagkaga Nama		Drawing Code					
Package Name	Package	Tape	Reel	Land			
SNT-4A	PF004-A-P-SD	PF004-A-C-SD	PF004-A-R-SD	PF004-A-L-SD			
SOT-23-5	MP005-A-P-SD	MP005-A-C-SD	MP005-A-R-SD	_			

3. Product name list

(1) SNT-4A

Table 1

Product name	Duty ratio change-start temperature Ts*1 [°C]	Duty ratio temperature sensitivity Ddt(s)*2 [%/°C]	Output form	Tsp5 ^{*3} [°C]	Т _{ЕМ5} * 4 [°С]
S-5855AACA-I4T1U	+40	-3	CMOS output	+45	+60
S-5855AEAA-I4T1U	+80	-1	CMOS output	+85	+125
S-5855AECA-I4T1U	+80	-3	CMOS output	+85	+100

*1. Ts: Duty ratio change-start temperature set by user

*2. Ddt(s): Duty ratio temperature sensitivity set by user

*3. T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_S (Refer to **Table 12** for details)

*4. T_{EM5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to Table 12 for details)

Remark Please contact our sales office for products other than those specified above.

(2) SOT-23-5

Table 2

Product name	Duty ratio change-start temperature Ts*1 [°C]	Duty ratio temperature sensitivity Ddt(s)*2 [%/°C]	Output form	T _{SP5} *³ [°C]	Т _{ЕМ5} * 4 [°С]
S-5855AAAA-M5T1U	+40	-1	CMOS output	+45	+115
S-5855AAAB-M5T1U	+40	-1	Nch open-drain output	+45	+115
S-5855AADA-M5T1U	+40	-4	CMOS output	+45	+55

*1. Ts: Duty ratio change-start temperature set by user

*2. Ddt(s): Duty ratio temperature sensitivity set by user

*3. T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_S (Refer to **Table 12** for details)

*4. T_{EM5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

Remark Please contact our sales office for products other than those specified above.

■ Pin Configurations

SNT-4A Top view

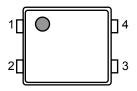


Figure 3

SOT-23-5 Top view

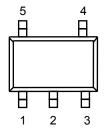


Figure 4

Table 3

Pin No.	Symbol	Pin Description
1	VSS	GND pin
2	CF	Connection pin for frequency control capacitor
3	VDD	Power supply pin
4	DOUT	Output pin

Table 4

Pin No.	Symbol	Pin Description
1	CF	Connection pin for frequency control capacitor
2	VSS	GND pin
3	NC*1	No connection
4	DOUT	Output pin
5	VDD	Power supply pin

^{*1.} The NC pin is electrically open.

The NC pin can be connected to VDD pin or VSS pin.

■ Absolute Maximum Ratings

Table 5

(Ta = +25°C, V_{SS} = 0 V, unless otherwise specified)

	Item	Symbol	Absolute Maximum Rating	Unit
Power supply voltage		V_{DD}	V _{SS} –0.3 to V _{SS} +7.0	V
Output voltage	CMOS output product	Vaur	V_{SS} -0.3 to V_{DD} $+0.3$	٧
Output voltage	Nch open-drain output product	V _{оит}	V_{SS} –0.3 to V_{SS} +7.0	V
CF voltage		V _{CF}	V_{SS} -0.3 to V_{DD} $+0.3$	V
Output current		Іоит	-13 to +13	mA
Dower dissination	SNT-4A	- P _D	300*1	mW
Power dissipation SOT-23-5		FD	600*1	mW
Operating ambient temperature		Topr	-40 to +125	°C
Storage temperatu	ıre	T _{stg}	−65 to +150	°C

^{*1.} When mounted on board

[Mounted board]

(1) Board size: 114.3 mm × 76.2 mm × t1.6 mm(2) Name: JEDEC STANDARD51-7

Caution The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

■ Electrical Characteristics

1. Common items

Table 6

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, unless otherwise specified)

			id 13F3, VDD 0.0 V, V33 0 V					
Item	Symbol	Con	dition	Min.	Тур.	Max.	Unit	Test circuit
Power supply voltage	V_{DD}		_	1.65	_	5.5	V	1
			Ta = T _{SP5}	_	-	200	μΑ	1
Current consumption	I _{DD}	No load at output pin	Ta = +25°C (Duty ratio 100%)	ı	50	-	μΑ	1
Output leakage current	ILEAK	Nch open-drain output produc V _{OUT} = 5.5 V, Ta = +25°C	-	_	1	μА	3	
Output source current	Isource	CMOS output product $V_{OUT} = V_{DD} - 0.3 \text{ V}$			_	_	mA	3
Output sink current	I _{SINK}	$V_{OUT} = V_{SS} + 0.3 \text{ V}$		3	-	_	mA	3
F-11 4:	1	$C_L = 100 \text{ pF}, R_L = 10 \text{ k}\Omega$	Nch open-drain output product	_	20	_	ns	5
Fall time	t _F	$V_{OUT} = 0.8 \times V_{DD}$ to $0.2 \times V_{DD}$	CMOS output product	-	20	_	ns	4
Diga tima	+ _	Nch open-drain output product $C_L = 15 \text{ pF}, R_L = 10 \text{ k}\Omega$ $V_{OUT} = 0.2 \times V_{DD}$ to $0.8 \times V_{DD}$		-	300	_	ns	5
Rise time	t _R	CMOS output product $C_L = 100 \text{ pF}, R_L = 10 \text{ k}\Omega$ $V_{OUT} = 0.2 \times V_{DD} \text{ to } 0.8 \times V_{DD}$	CMOS output product $C_L = 100 \text{ pF}, R_L = 10 \text{ k}\Omega$			_	ns	4

2. Product with duty ratio temperature sensitivity $Ddt(s) = -1 \%/^{\circ}C$

Table 7

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, C_{FREQ} = 2.2 nF, unless otherwise specified)

Item	Symbol		Condition	Min.	Тур.	Max.	Unit	Test circuit
Duty ratio accuracy	Dane	$V_{DD} = 3.0 \text{ V}$		92.0	95.0	98.0	%	2
Duty ratio accuracy	Dsp5	$V_{DD} = 1.65 \text{ V}$	to 5.5 V	91.0	95.0	99.0	%	2
Duty ratio temperature	D44/E)*1	$Ta = T_{SP5}^{*2}$,	$V_{DD} = 3.0 \text{ V}$	-1.2	-1.0	-0.8	%/°C	2
sensitivity	Dai(E)	T _{EM5} *3	V_{DD} = 1.65 V to 5.5 V	-1.26	-1.0	-0.76	%/°C	2
		Т Т	$V_{DD} = 3.0 \text{ V}$	1950	2300	2650	Hz	2
Oscillation frequency	fosc	Ta = T _{SP5}	V_{DD} = 1.65 V to 5.5 V	1860	2300	2780	Hz	2
		Ta = T _{EM5}	V _{DD} = 3.0 V	1670	2300	3040	Hz	2

^{*1.} Ddt(E): Actual duty ratio temperature sensitivity

3. Product with duty ratio temperature sensitivity $Ddt(s) = -2 \%/^{\circ}C$

Table 8

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, C_{FREQ} = 4.7 nF, unless otherwise specified)

			,	- ,		,		
Item	Symbol		Conditions		Тур.	Max.	Unit	Test circuit
Duty ratio accuracy	Dane	$V_{DD} = 3.0 \text{ V}$		84.0	90.0	96.0	%	2
Duty ratio accuracy	Dsp5	$V_{DD} = 1.65 \text{ V}$	to 5.5 V	82.0	90.0	98.0	%	2
Duty ratio temperature	D4+/E)*1	$Ta = T_{SP5}^{*2}$	$V_{DD} = 3.0 \text{ V}$	-2.4	-2.0	-1.6	%/°C	2
sensitivity	Dal(E)	T _{EM5} *3	V_{DD} = 1.65 V to 5.5 V	-2.52	-2.0	-1.52	%/°C	2
		T T	$V_{DD} = 3.0 \text{ V}$	1840	2160	2740	Hz	2
Oscillation frequency	fosc	Ta = T _{SP5}	V_{DD} = 1.65 V to 5.5 V	1750	2160	2600	Hz	2
		Ta = T _{EM5}	$V_{DD} = 3.0 \text{ V}$	1560	2160	2850	Hz	2

^{*1.} Ddt(E): Actual duty ratio temperature sensitivity

^{*2.} T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_S (Refer to **Table 12** for details)

^{*3.} T_{EM5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

^{*2.} T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_S (Refer to **Table 12** for details)

^{*3.} T_{EM5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

4. Product with duty ratio temperature sensitivity $Ddt(s) = -3 \%/^{\circ}C$

Table 9

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, C_{FREQ} = 6.8 nF, unless otherwise specified)

Items	Symbol		Conditions	Min.	Тур.	Max.	Unit	Test circuit
Duty ratio accuracy	Dane	$V_{DD} = 3.0 \text{ V}$		76.0	85.0	94.0	%	2
Duty ratio accuracy	Dsp5	$V_{DD} = 1.65$	V to 5.5 V	73.0	85.0	97.0	%	2
Duty ratio temperature	D4+/E)*1	$Ta = T_{SP5}^{*2}$	$V_{DD} = 3.0 \text{ V}$	-3.6	-3.0	-2.4	%/°C	2
sensitivity	Dal(E)	T _{EM5} *3	V_{DD} = 1.65 V to 5.5 V	-3.78	-3.0	-2.28	%/°C	2
		т. – т	$V_{DD} = 3.0 \text{ V}$	1900	2240	2570	Hz	2
Oscillation frequency	fosc	Ta = T _{SP5}	V_{DD} = 1.65 V to 5.5 V	1810	2240	2700	Hz	2
		Ta = T _{EM5}	$V_{DD} = 3.0 \text{ V}$	1620	2240	2950	Hz	2

^{*1.} Ddt(E): Actual duty ratio temperature sensitivity

5. Product with duty ratio temperature sensitivity $Ddt(s) = -4 \%/^{\circ}C$

Table 10

(Ta = T_{SP5}, V_{DD} = 3.0 V, V_{SS} = 0 V, C_{FREQ} = 10 nF, unless otherwise specified)

			14 - 13F5, VDD - 0.0 V,	V33 U V,	OTIVE 10	in , arneod	J Oli ICI WIO	c specifica)				
Items	Symbol		Conditions	Min.	Тур.	Max.	Unit	Test circuit				
Duty ratio accuracy	Dane	$V_{DD} = 3.0 \text{ V}$		68.0	80.0	92.0	%	2				
Duty ratio accuracy	Dsp5	$V_{DD} = 1.65$	V to 5.5 V	64.0	80.0	96.0	%	2				
Duty ratio temperature	Dd+/C)*1	$Ta = T_{SP5}^{*2}$	$V_{DD} = 3.0 \text{ V}$	-4.8	-4.0	-3.2	%/°C	2				
sensitivity	Dal(E)	T _{EM5} *3	V_{DD} = 1.65 V to 5.5 V	-5.05	-4.0	-3.04	%/°C	2				
		To - T	$V_{DD} = 3.0 \text{ V}$	1730	2030	2330	Hz	2				
Oscillation frequency	fosc	fosc	fosc	fosc	fosc	Ta = T _{SP5}	V_{DD} = 1.65 V to 5.5 V	1640	2030	2440	Hz	2
		Ta = T _{EM5}	$V_{DD} = 3.0 \text{ V}$	1470	2030	2680	Hz	2				

^{*1.} Ddt(E): Actual duty ratio temperature sensitivity

^{*2.} T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_S (Refer to **Table 12** for details)

^{*3.} T_{Em5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

^{*2.} T_{SP5}: Temperature 5°C higher than duty ratio change-start temperature T_S (Refer to **Table 12** for details)

^{*3.} T_{EM5}: Higher temperature when measuring duty ratio temperature sensitivity (Refer to **Table 12** for details)

■ Test Circuits

1.

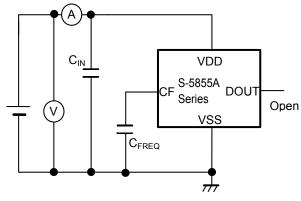
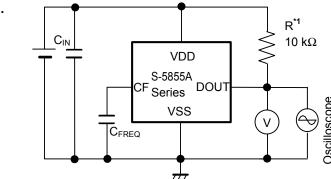


Figure 5

2.



***1.** Resistor (R) is unnecessary for the CMOS output product. **Figure 6**

3.

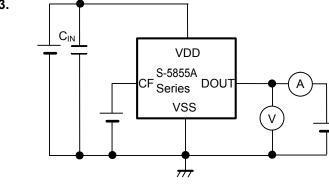
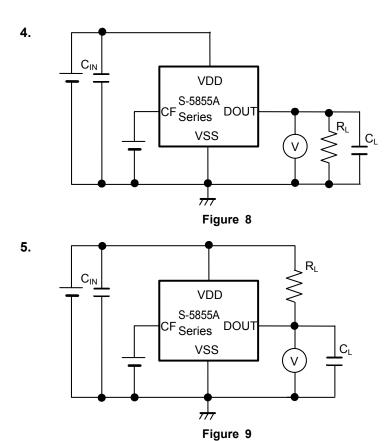
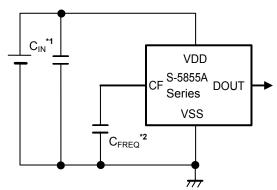


Figure 7



■ Standard Circuit



- *1. C_{IN} is a capacitor for stabilization.
- *2. CFREQ is a capacitor for oscillation frequency.

Figure 10

Caution The above connection diagram and constant will not guarantee successful operation. Perform thorough evaluation using the actual application to set the constant.

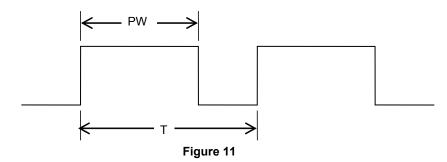
■ Operation

1. Duty ratio

The following equation is the definition of duty ratio.

Duty ratio = PW / $T \times 100$ [%]

The definitions of PW and T are shown in Figure 11.



2. Oscillation frequency

The oscillation frequency is set by the capacitance value of the capacitor C_{FREQ} for the oscillation frequency. The relationship between the C_{FREQ} capacitance value of each duty ratio temperature sensitivity and the center value of the oscillation frequency are shown in **Table 11**.

Table 11

Duty ratio temperature sensitivity	C _{FREQ} capacitance value	Center value of oscillation frequency
Ddt(s) [%/°C]	[nF]	[Hz]
-1	2.2	2300
-2	4.7	2160
-3	6.8	2240
-4	10.0	2030

■ Explanation of Terms

1. Duty ratio accuracy (Dsp5)

Dsp5 shows duty ratio in temperature T_{SP5} 5°C higher than duty ratio change-start temperature T_{S} .

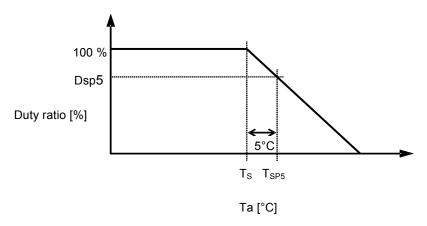
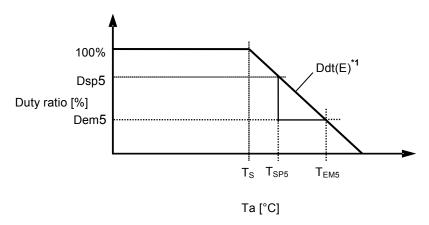


Figure 12

2. Duty ratio temperature sensitivity (Ddt(E))

Duty ratio temperature sensitivity (Ddt(E)) is the temperature coefficient of duty ratio calculated from the output duty ratio at Ta = T_{SP5} and Ta = T_{EM5} . T_{EM5} is the temperature decided for each product shown in **Table 11**, and Dem5 is the output duty ratio at Ta = T_{EM5} . Ddt(E) is calculated using the following formula.

$$Ddt(E) = (Dem5 - Dsp5) / (T_{EM5} - T_{SP5}) [\%/^{\circ}C]$$



*1. Selectable from -1 %/°C to -4 %/°C in 1 %/°C step

Figure 13

Table 12 T_{SP5} and T_{EM5} in Each Product

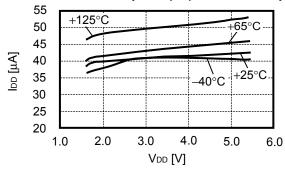
Duty ratio change-start temperature T _S [°C]	Duty ratio temperature sensitivity Ddt(s) [%/°C]	T _{SP5} [°C]	T _{EM5} [°C]
+40	-1	+45	+115
+40	-2	+45	+75
+40	-3	+45	+60
+40	-4	+45	+55
+50	-1	+55	+125
+50	-2	+55	+85
+50	-3	+55	+70
+50	-4	+55	+65
+60	–1	+65	+125
+60	-2	+65	+95
+60	-3	+65	+80
+60	-4	+65	+75
+70	–1	+75	+125
+70	-2	+75	+105
+70	-3	+75	+90
+70	-4	+75	+85
+80	-1	+85	+125
+80	-2	+85	+115
+80	-3	+85	+100
+80	-4	+85	+95

■ Precaution

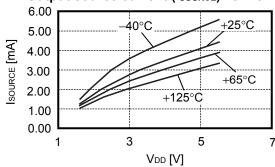
- Note that this IC may itself heat depending on a connected load to the output pin, resulting in error in measuring temperature.
- Set a capacitor (C_{IN}) of approx. 0.1 µF between the VDD pin and VSS pin for stabilization as close to IC as possible.
- Connect a capacitor C_{FREQ} for oscillation frequency as close to IC as possible.
- Leakage current applied on the CF pin may cause error in the output duty ratio. Do not connect other components than C_{FREQ}.
- Since the error of the output duty ratio may become large depending on an application circuit or the design of a board pattern on this IC, perform thorough evaluation with the actually mounted model in the case of use.
- The application conditions for the input voltage, output voltage, and load current should not exceed the package power dissipation.
- Do not apply an electrostatic discharge to this IC that exceeds the performance ratings of the built-in electrostatic protection circuit.
- SII Semiconductor Corporation claims no responsibility for any disputes arising out of or in connection with any infringement by products, including this IC, of patents owned by a third party.

■ Characteristics (Typical Data)

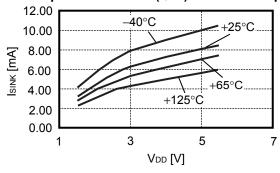
1. Current consumption (IDD) vs. Power supply voltage (VDD)



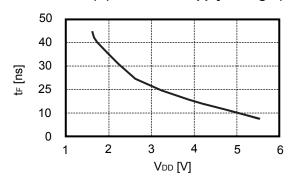
2. Output source current (Isource) vs. Power supply voltage (VDD)



3. Output sink current (I_{SINK}) vs. Power supply voltage (V_{DD})

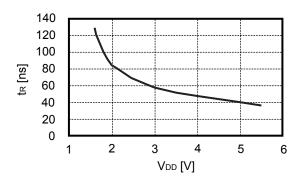


4. Fall time (t_F) vs. Power supply voltage (V_{DD}) dependency

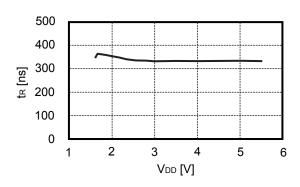


5. Rise time (t_R) vs.Power supply voltage (V_{DD}) dependency

5.1 CMOS output product

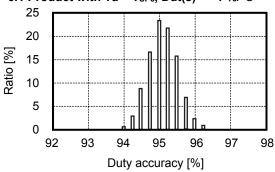


5.2 Nch open-drain output product

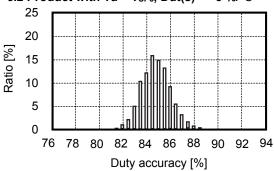


6. Duty ratio accuracy

6.1 Product with Ta = T_{SP5} , Ddt(s) = -1 %/°C

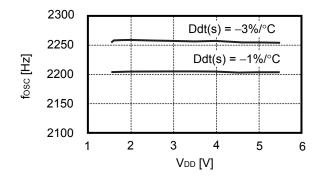


6.2 Product with Ta = T_{SP5} , Ddt(s) = $-3 \% / ^{\circ}C$

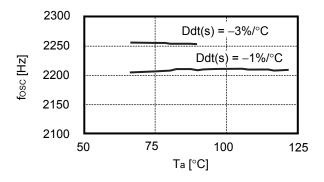


7. Oscillation frequency

7.1 Oscillation frequency (fosc) vs. Power supply voltage (VDD)



7.2 Oscillation frequency (fosc) vs. Temperature(Ta)

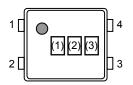


■ Marking Specifications

(1) SNT-4A

SNT-4A Top view

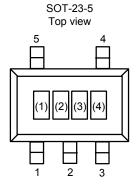
(1) to (3): Product code (Refer to Product name vs. Product code.)



Product name vs. Product code

Product Name	Product Code		
Product Name	(1)	(2)	(3)
S-5855AACA-I4T1U	V	Q	С
S-5855AEAA-I4T1U	V	Q	Υ
S-5855AECA-I4T1U	V	Q	3

(2) SOT-23-5

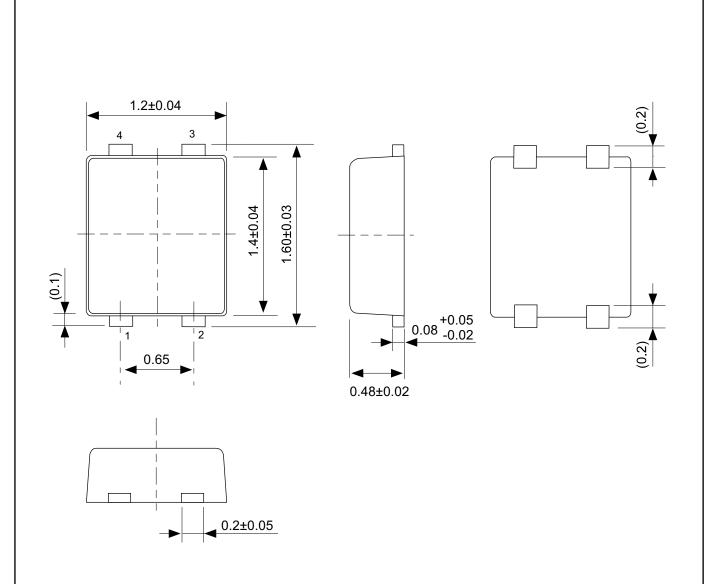


(1) to (3): Product code (refer to Product name vs. Product code)

(4): Lot number

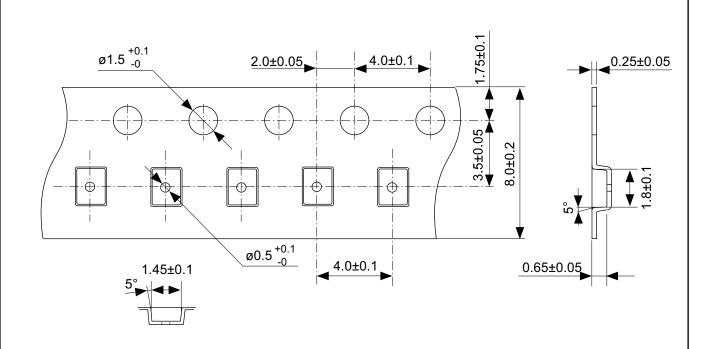
Product name vs. Product code

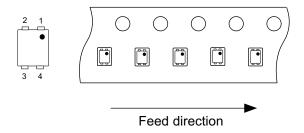
Draduct Name	Product Code		
Product Name	(1)	(2)	(3)
S-5855AAAA-M5T1U	V	Q	Α
S-5855AAAB-M5T1U	V	R	Α
S-5855AADA-M5T1U	V	Q	D



No. PF004-A-P-SD-4.0

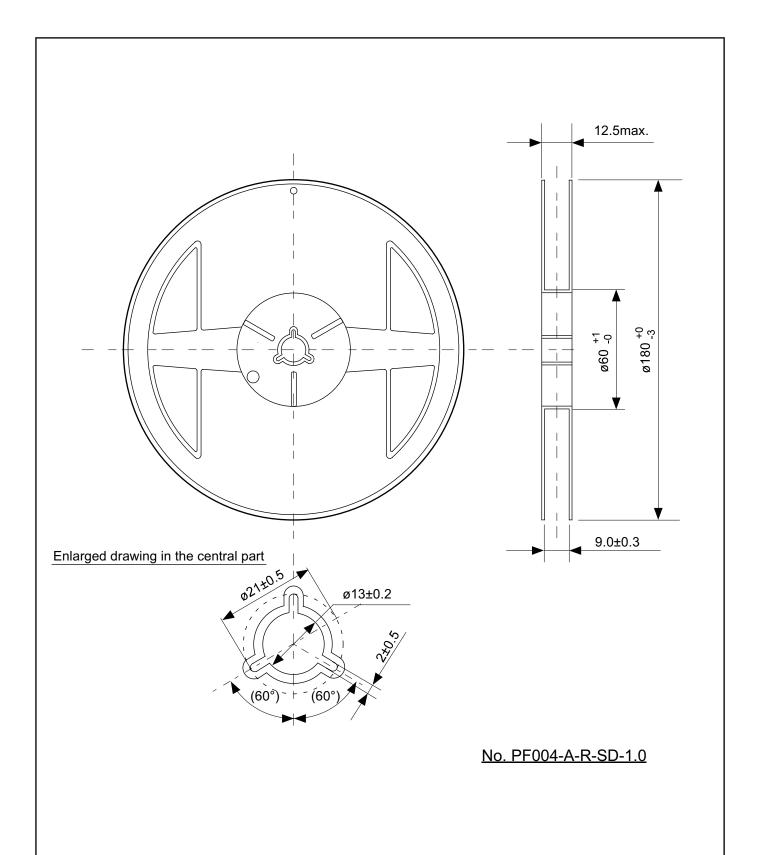
TITLE	SNT-4A-A-PKG Dimensions	
No.	PF004-A-P-SD-4.0	
SCALE		
UNIT	mm	
011.0		
SII Semiconductor Corporation		





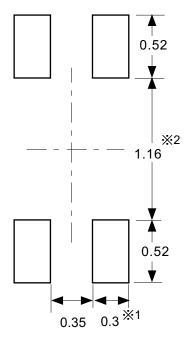
No. PF004-A-C-SD-1.0

TITLE	SNT-4A-A-Carrier Tape
No.	PF004-A-C-SD-1.0
SCALE	
UNIT	mm
SII Se	emiconductor Corporation



TITLE	SNT-4A-A-Reel		
No.	PF004-A-R-SD-1.0		
SCALE		QTY.	5,000
UNIT	mm		
SII Semiconductor Corporation			

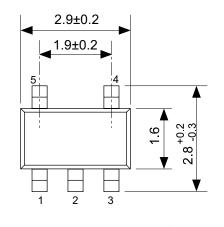
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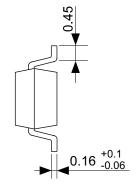


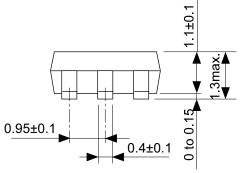
- %1. ランドパターンの幅に注意してください (0.25 mm min. / 0.30 mm typ.)。 %2. パッケージ中央にランドパターンを広げないでください (1.10 mm ~ 1.20 mm)。
- 注意 1. パッケージのモールド樹脂下にシルク印刷やハンダ印刷などしないでください。
 - 2. パッケージ下の配線上のソルダーレジストなどの厚みをランドパターン表面から0.03 mm 以下にしてください。
 - 3. マスク開口サイズと開口位置はランドパターンと合わせてください。
 - 4. 詳細は "SNTパッケージ活用の手引き"を参照してください。
- ※1. Pay attention to the land pattern width (0.25 mm min. / 0.30 mm typ.).
- ※2. Do not widen the land pattern to the center of the package (1.10 mm to 1.20 mm).
- Caution 1. Do not do silkscreen printing and solder printing under the mold resin of the package.
 - 2. The thickness of the solder resist on the wire pattern under the package should be 0.03 mm or less from the land pattern surface.
 - 3. Match the mask aperture size and aperture position with the land pattern.
 - 4. Refer to "SNT Package User's Guide" for details.
- ※1. 请注意焊盘模式的宽度 (0.25 mm min. / 0.30 mm typ.)。
- ※2. 请勿向封装中间扩展焊盘模式 (1.10 mm ~ 1.20 mm)。
- 注意 1. 请勿在树脂型封装的下面印刷丝网、焊锡。
 - 2. 在封装下、布线上的阻焊膜厚度 (从焊盘模式表面起) 请控制在 0.03 mm 以下。
 - 3. 钢网的开口尺寸和开口位置请与焊盘模式对齐。
 - 4. 详细内容请参阅 "SNT 封装的应用指南"。

No. PF004-A-L-SD-4.1

TITLE	SNT-4A-A -Land Recommendation	
No.	PF004-A-L-SD-4.1	
SCALE		
UNIT	mm	
011.0		
SII Semiconductor Corporation		

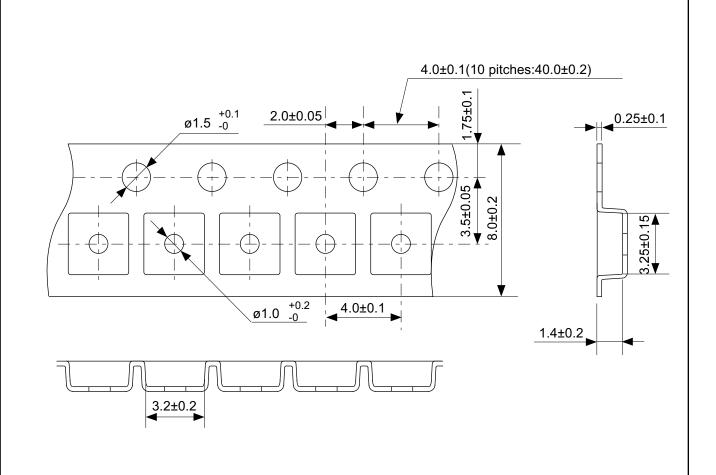


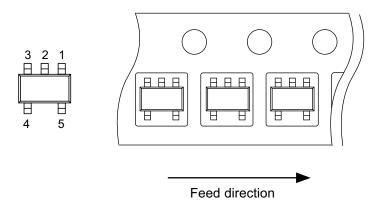




No. MP005-A-P-SD-1.2

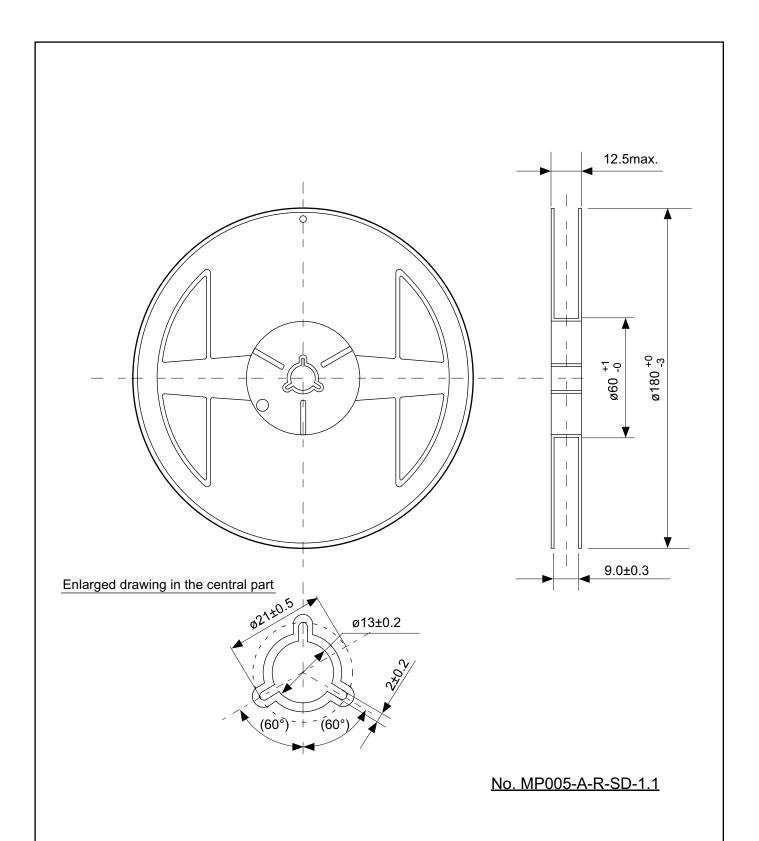
TITLE	SOT235-A-PKG Dimensions	
No.	MP005-A-P-SD-1.2	
SCALE		
UNIT	mm	
SII Semiconductor Corporation		





No. MP005-A-C-SD-2.1

TITLE	SOT235-A-Carrier Tape
No.	MP005-A-C-SD-2.1
SCALE	
UNIT	mm
SII S	emiconductor Corporation



TITLE	SOT235-A-Reel		
No.	MP005-A-R-SD-1.1		
SCALE		QTY.	3,000
UNIT	mm		
SII Semiconductor Corporation			

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